

- Selective Ion Beam Etching of 100 mm wafers
- Typical wafer is divided into 232 etching areas and each area is etched for a user specified time
- Continuous wafer motion during the etching process provides a smooth etching profile
- Applications include improving the frequency distribution of SAW and FBAR wafers



Transport Boat
(bottom view)

- Elevator subsystem continuously handles two magazines
- Each magazine holds five transport boats
- Transport boat carries two 100 mm wafers
- Wafers are continuously loaded, etched, and unloaded
- User specified etching times are communicated to the system via network or floppy disk in a text file format

SPECIFICATIONS

Typical Uniformity Improvement:

5 Times

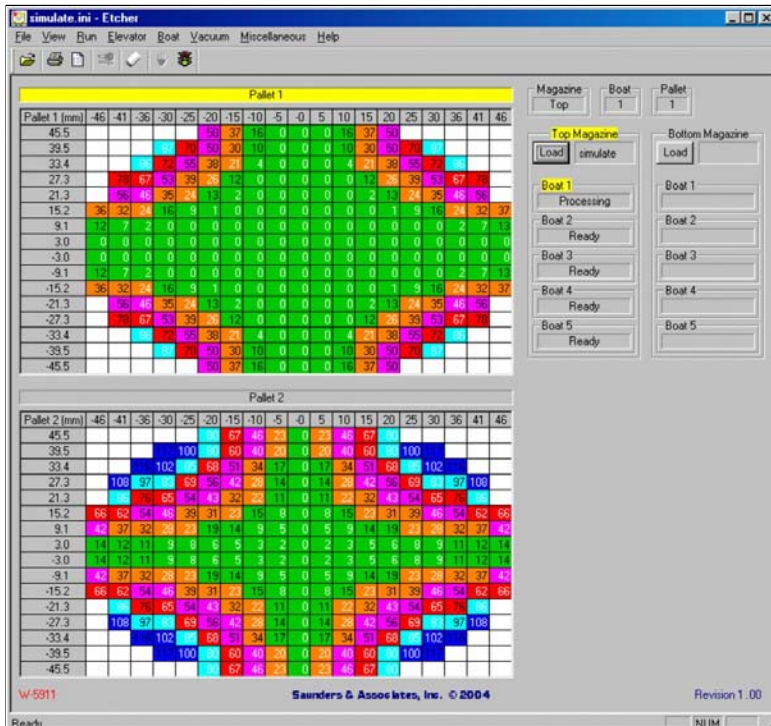
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SYSTEM CONFIGURATION

- Direct Drive Roughing Pump
- Computer
- Cryo Pump
- System Software
- Ion Gun
- Light Pole
- Elevator Subsystem

SCREEN FORMAT



Example wafer etching times in seconds

FACILITY REQUIREMENTS

- **Power:** 208VAC 3-Phase, 7KVA, 50/60 Hz
- **Inlet Pressure:** 90 - 100 PSIG
 - Air: 90 - 100 PSIG
 - Nitrogen: 70 - 100 PSIG
 - Process Gas: 20 PSIG
- **Dimensions:** W 53" x D 37" x H 88"

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